

	<b>E502650</b>
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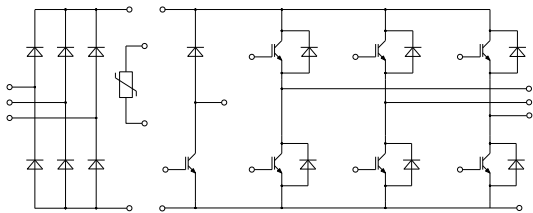
**Features**

- Low Switching Losses
- Low  $V_{ce(sat)}$  with Positive Temperature Coefficient
- Including Fast & Soft Recovery Anti-parallel FWD
- Low Inductance Case
- High Short Circuit Capability(10 $\mu$ s)
- Maximum Junction Temperature 175°C
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

**Applications**

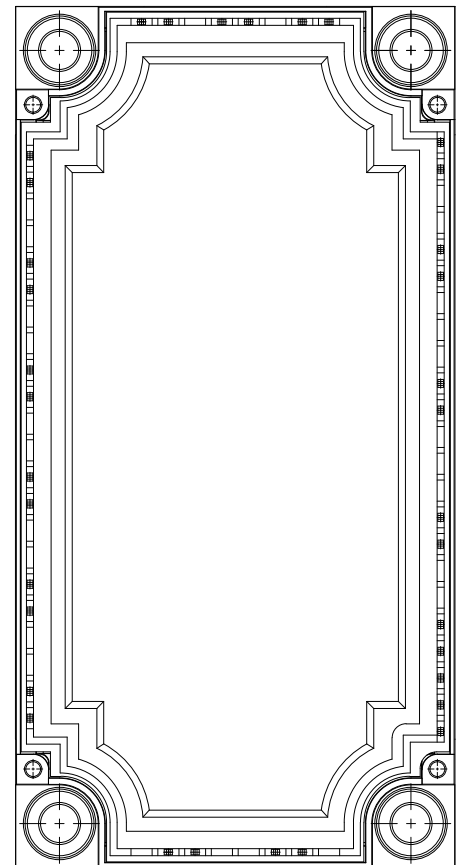
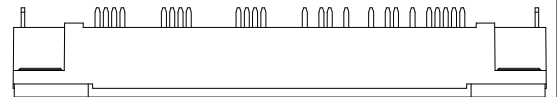
- Motor Drivers
- AC and DC Servo Drive Amplifier
- UPS (Uninterruptible Power Supplies)

**Circuit Diagram**



**IGBT Modules  
1200V 75A**

E2A



● IGBT- Inverter

Maximum Ratings

Parameter	Symbol	Test Conditions	Rating	Unit
Collector-Emitter Voltage	$V_{CES}$	$V_{GE}=0V, I_C=1mA, T_{vj}=25^{\circ}C$	1200	V
Continuous Collector Current	$I_C$	$T_C=80^{\circ}C, T_{vjmax}=175^{\circ}C$	75	A
Repetitive Peak Collector Current	$I_{CRM}$	$t_p=1ms$	150	A
Gate-Emitter Voltage	$V_{GES}$	$T_{vj}=25^{\circ}C$	$\pm 20$	V
Total Power Dissipation	$P_{tot}$	$T_C=25^{\circ}C, T_{vjmax}=175^{\circ}C$	470	W

Electrical Characteristics

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=3.3mA, T_{vj}=25^{\circ}C$	5	5.8	6.5	V
Collector-Emitter Cut-off Current	$I_{CES}$	$V_{CE}=1200V, V_{GE}=0V, T_{vj}=25^{\circ}C$			1	mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=75A, V_{GE}=15V, T_{vj}=25^{\circ}C$		1.95		V
		$I_C=75A, V_{GE}=15V, T_{vj}=125^{\circ}C$		2.20		V
		$I_C=75A, V_{GE}=15V, T_{vj}=150^{\circ}C$		2.30		V
Gate Charge	$Q_g$			0.85		$\mu C$
Input Capacitance	$C_{ies}$	$V_{CE}=25V, V_{GE}=0V, f=1MHz$		4.2		nF
Reverse Transfer Capacitance	$C_{res}$			0.32		
Internal Gate Resistance	$R_{gint}$			10		$\Omega$
Gate-Emitter leakage current	$I_{GES}$	$V_{CE}=0V, V_{GE}=20V, T_{vj}=25^{\circ}C$			400	nA
Turn-On Delay Time	$t_{d(on)}$	$V_{CE}=600V, I_C=75A, V_{GE}=\pm 15V, R_G=2.2\Omega, T_{vj}=25^{\circ}C$		75		ns
Rise Time	$t_r$			40		
Turn-Off Delay Time	$t_{d(off)}$			163		
Fall Time	$t_f$			235		
Turn-On Energy	$E_{on}$			4.71		
Turn-Off Energy	$E_{off}$		5.45			
Turn-On Delay Time	$t_{d(on)}$	$V_{CE}=600V, I_C=75A, V_{GE}=\pm 15V, R_G=2.2\Omega, T_{vj}=150^{\circ}C$		77		ns
Rise Time	$t_r$			47		
Turn-Off Delay Time	$t_{d(off)}$			173		
Fall Time	$t_f$			309		
Turn-On Energy	$E_{on}$			6.73		
Turn-Off Energy	$E_{off}$		6.24			
SC Data	$I_{SC}$	$T_p \leq 10\mu s, V_{GE}=15V, T_{vj}=150^{\circ}C, V_{CC}=900V, V_{CEM} \leq 1200V$		300		A

● Diode- Inverter

Maximum Ratings

Parameter	Symbol	Test Conditions	Rating	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	$T_{vj}=25^{\circ}C$	1200	V
Continuous DC Forward Current	$I_F$		75	A
Repetitive Peak Forward Current	$I_{FRM}$	$t_p=1ms$	150	A
$I^2t$ -value	$I^2t$	$V_R=0, t_p=10ms, T_{vj}=125^{\circ}C$	810	$A^2s$
		$V_R=0, t_p=10ms, T_{vj}=150^{\circ}C$	690	

Electrical Characteristics

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Voltage	$V_F$	$I_F=75A, T_{vj}=25^{\circ}C$		1.95	2.60	V
		$I_F=75A, T_{vj}=125^{\circ}C$		1.78		V
		$I_F=75A, T_{vj}=150^{\circ}C$		1.70		V
Recovered Charge	$Q_{rr}$	$I_F=75A, V_R=600V,$ $-di_F/dt=1700A/\mu s,$ $T_{vj}=25^{\circ}C$		2.1		$\mu C$
Peak Reverse Recovery Current	$I_{rr}$			53		A
Reverse Recovery Energy	$E_{rec}$			0.35		mJ
Recovered Charge	$Q_{rr}$	$I_F=75A, V_R=600V,$ $-di_F/dt=1700A/\mu s,$ $T_{vj}=150^{\circ}C$		5.8		$\mu C$
Peak Reverse Recovery Current	$I_{rr}$			56		A
Reverse Recovery Energy	$E_{rec}$			1.67		mJ

● IGBT- Brake-chopper

Maximum Ratings

Parameter	Symbol	Test Conditions	Rating	Unit
Collector-Emitter Voltage	$V_{CES}$	$V_{GE}=0V, I_C=1mA, T_{vj}=25^{\circ}C$	1200	V
Continuous Collector Current	$I_C$	$T_C=100^{\circ}C, T_{vjmax}=175^{\circ}C$	50	A
Repetitive Peak Collector Current	$I_{CRM}$	$t_p=1ms$	100	A
Gate-Emitter Voltage	$V_{GES}$	$T_{vj}=25^{\circ}C$	$\pm 20$	V
Total Power Dissipation	$P_{tot}$	$T_C=25^{\circ}C, T_{vjmax}=175^{\circ}C$	442	W

Electrical Characteristics

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit	
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=1.7mA, T_{vj}=25^{\circ}C$	5.0	5.7	6.5	V	
Collector-Emitter Cut-off Current	$I_{CES}$	$V_{CE}=1200V, V_{GE}=0V, T_{vj}=25^{\circ}C$			1	mA	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=50A, V_{GE}=15V, T_{vj}=25^{\circ}C$		1.9		V	
		$I_C=50A, V_{GE}=15V, T_{vj}=125^{\circ}C$		2.25		V	
		$I_C=50A, V_{GE}=15V, T_{vj}=150^{\circ}C$		2.32		V	
Gate Charge	$Q_g$			0.35		$\mu C$	
Input Capacitance	$C_{ies}$	$V_{CE}=25V, V_{GE}=0V, f=1MHz$		2.60		nF	
Reverse Transfer Capacitance	$C_{res}$			0.10			
Gate-Emitter leakage current	$I_{GES}$	$V_{CE}=0V, V_{GE}=20V, T_{vj}=25^{\circ}C$			400	nA	
Turn-On Delay Time	$t_{d(on)}$	$V_{CE}=600V, I_C=50A, V_{GE}=\pm 15V, R_G=20\Omega, T_{vj}=25^{\circ}C$		41		ns	
Rise Time	$t_r$			48			
Turn-Off Delay Time	$t_{d(off)}$			160			
Fall Time	$t_f$			244			
Turn-On Energy	$E_{on}$				5.92		mJ
Turn-Off Energy	$E_{off}$			3.39			
Turn-On Delay Time	$t_{d(on)}$	$V_{CE}=600V, I_C=50A, V_{GE}=\pm 15V, R_G=20\Omega, T_{vj}=150^{\circ}C$		45		ns	
Rise Time	$t_r$			50			
Turn-Off Delay Time	$t_{d(off)}$			169			
Fall Time	$t_f$			302			
Turn-On Energy	$E_{on}$				6.87		mJ
Turn-Off Energy	$E_{off}$				3.73		
SC Data	$I_{SC}$	$T_p \leq 10\mu s, V_{GE}=15V, T_{vj}=150^{\circ}C, V_{CC}=900V, V_{CEM} \leq 1200V$		200		A	

## ● Diode- Brake-chopper

### Maximum Ratings

Parameter	Symbol	Test Conditions	Rating	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	$T_{vj}=25^{\circ}C$	1200	V
Continuous DC Forward Current	$I_F$		35	A
Repetitive Peak Forward Current	$I_{FRM}$	$t_p=1ms$	70	A
$I^2t$ -value	$I^2t$	$V_R=0, t_p=10ms, T_{vj}=125^{\circ}C$	240	$A^2s$
		$V_R=0, t_p=10ms, T_{vj}=150^{\circ}C$	220	

### Electrical Characteristics

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Voltage	$V_F$	$I_F=35A, T_{vj}=25^{\circ}C$		1.95		V
		$I_F=35A, T_{vj}=125^{\circ}C$		1.78		V
		$I_F=35A, T_{vj}=150^{\circ}C$		1.69		V
Recovered Charge	$Q_{rr}$	$I_F=35A, V_R=600V,$ $-di_F/dt=1600A/\mu s, T_{vj}=25^{\circ}C$		2.35		$\mu C$
Peak Reverse Recovery Current	$I_{rr}$			21		A
Reverse Recovery Energy	$E_{rec}$			0.67		mJ
Recovered Charge	$Q_{rr}$	$I_F=35A, V_R=600V,$ $-di_F/dt=1600A/\mu s, T_{vj}=150^{\circ}C$		3.81		$\mu C$
Peak Reverse Recovery Current	$I_{rr}$			25		A
Reverse Recovery Energy	$E_{rec}$			1.13		mJ

## ● Diode- Rectifier

### Maximum Ratings

Parameter	Symbol	Test Conditions	Rating	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	$T_j=25^{\circ}\text{C}$	1600	V
Average On-state Current 50/60Hz, sine wave	$I_{F(AV)}$	$T_C=100^{\circ}\text{C}$	80	A
Maximum RMS Current at Rectifier Output	$I_{RMSM}$	$T_C=100^{\circ}\text{C}$	120	A
Surge Forward Current	$I_{FSM}$	$V_R=0, t_p=10\text{ms}, T_{vj}=25^{\circ}\text{C}$	1200	A
		$V_R=0, t_p=10\text{ms}, T_{vj}=150^{\circ}\text{C}$	1000	A
$I^2t$ -value	$I^2t$	$V_R=0, t_p=10\text{ms}, T_{vj}=25^{\circ}\text{C}$	7200	$\text{A}^2\text{s}$
		$V_R=0, t_p=10\text{ms}, T_{vj}=150^{\circ}\text{C}$	5000	$\text{A}^2\text{s}$

### Electrical Characteristics

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Diode Forward Voltage	$V_F$	$I_F=50\text{A}, T_j=125^{\circ}\text{C}$		0.98		V
Reverse Current	$I_r$	$T_{vj}=125^{\circ}\text{C}, V_R=1600\text{V}$			2	mA

## ● NTC-Thermistor

### Electrical Characteristics

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Rated Resistance	$R_{25}$			5		k $\Omega$
Deviation of R100	$\Delta R/R$	$T_C=100, R_{100}=493.3\Omega$	-5		5	%
Power Dissipation	$P_{25}$				20	mW
B-value	$B_{25/50}$	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15\text{K}))]$		3375		K

**● Module Characteristics( $T_C=25^{\circ}\text{C}$  unless otherwise specified)**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Isolation voltage	$V_{\text{isol}}$	$t=1\text{ min}, f=50\text{ Hz}$	2500			V
Maximum Junction Temperature	$T_{\text{jmax}}$				175	$^{\circ}\text{C}$
Operating Junction Temperature	$T_{\text{vj op}}$		-40		150	$^{\circ}\text{C}$
Operating Junction Temperature	$T_{\text{stg}}$		-40		125	$^{\circ}\text{C}$
Stray Inductance	$L_{\text{CE}}$			60		nH
Module Lead Resistance , Terminal to Chip	$R_{\text{cc'+EE'}}$	$T_C=25^{\circ}\text{C}$ , per switch		4		m $\Omega$
	$R_{\text{AA'+CC'}}$			3		
Thermal Resistance Junction to Case	$R_{\theta\text{jc}}$	per IGBT-inverter		0.315		K/W
		per Diode-inverter		0.619		
		per IGBT-brake-chopper		0.5		
		per Diode-chopper		1.266		
		per Diode-rectifier		0.635		
Thermal Resistance Case to Sink	$R_{\theta\text{cs}}$	per IGBT-inverter		0.121		K/W
		per Diode-inverter		0.221		
		per IGBT-brake-chopper		0.18		
		per Diode-chopper		0.452		
		per Diode-rectifier		0.227		
		per Module		0.009		
Module-to-Sink Torque	$M_S$		3		6	N·m
Weight of Module	G			300		g

### Curve Characteristics

Fig1.IGBT Output Characteristics

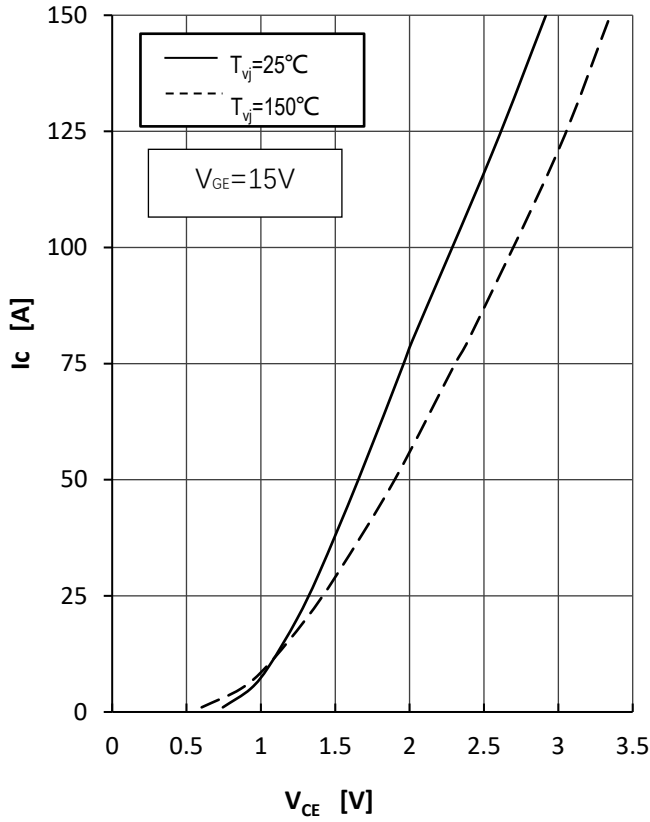


Fig2.IGBT Transfer Characteristics

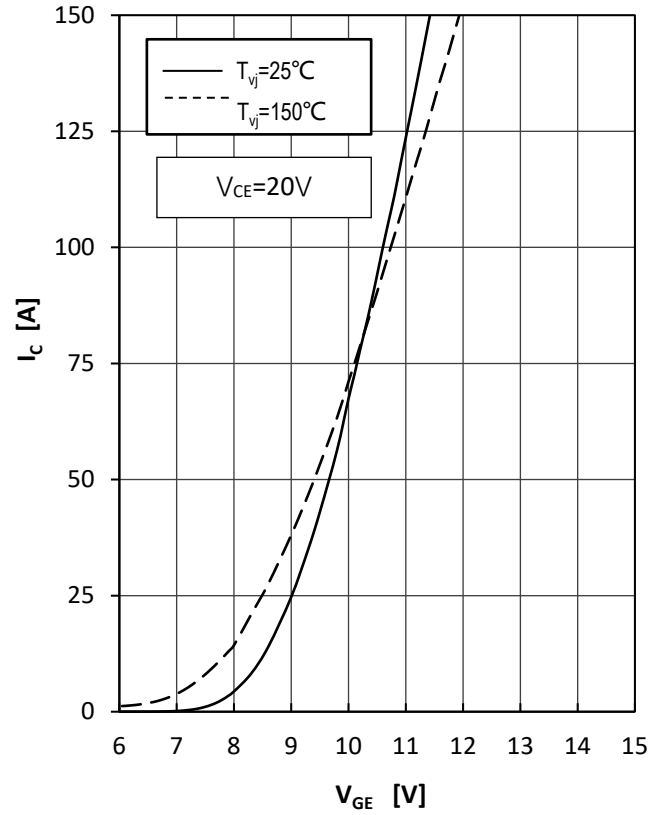


Fig3.IGBT Switching Loss vs.Ic

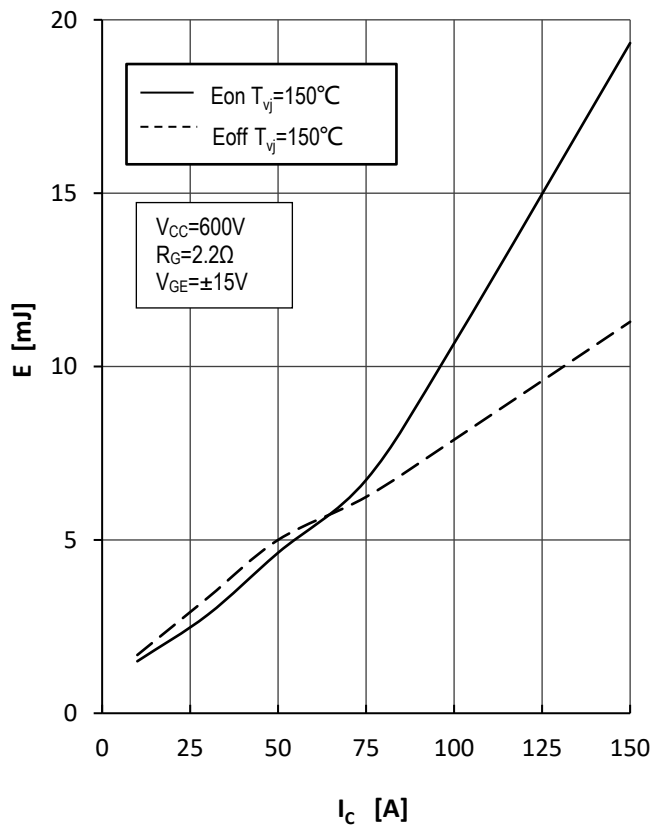
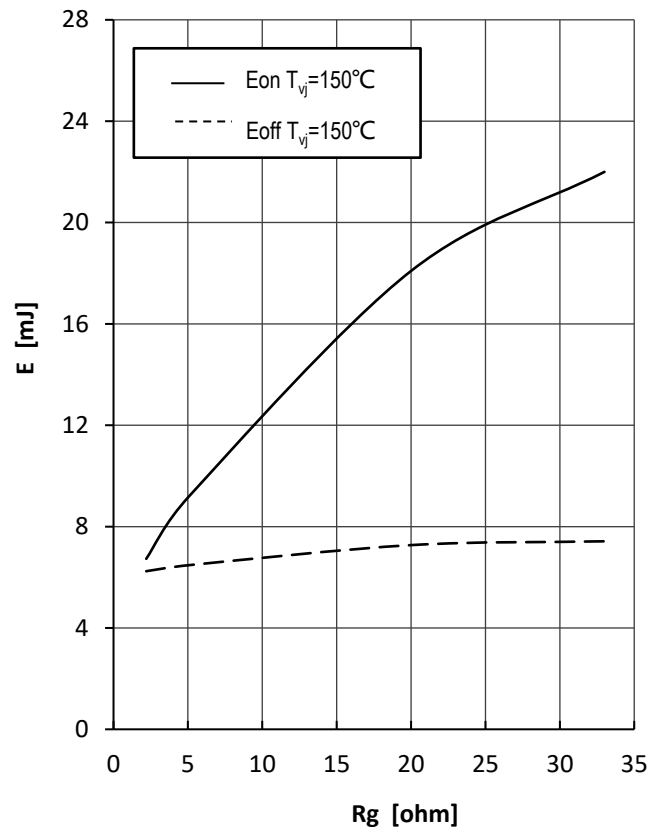


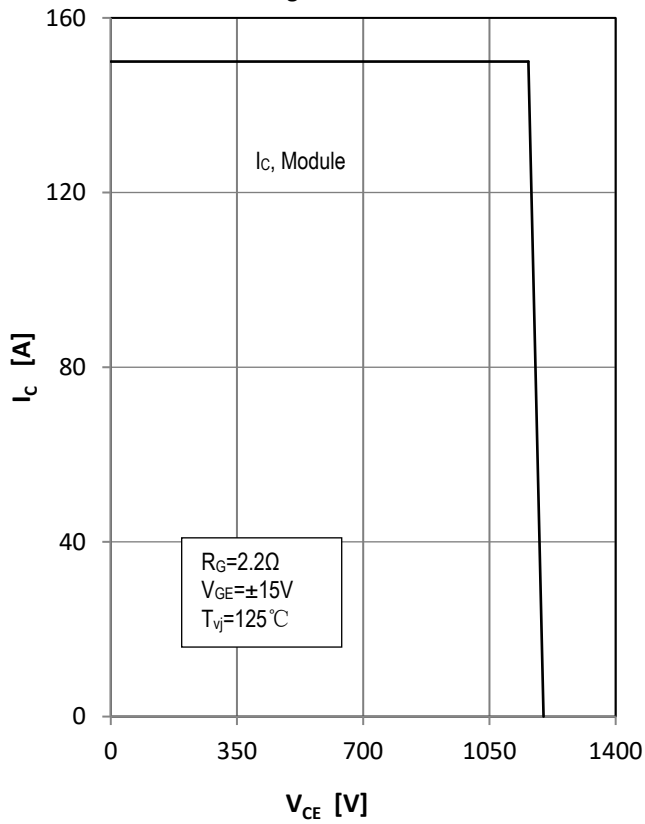
Fig4.IGBT Switching Loss vs.Rg



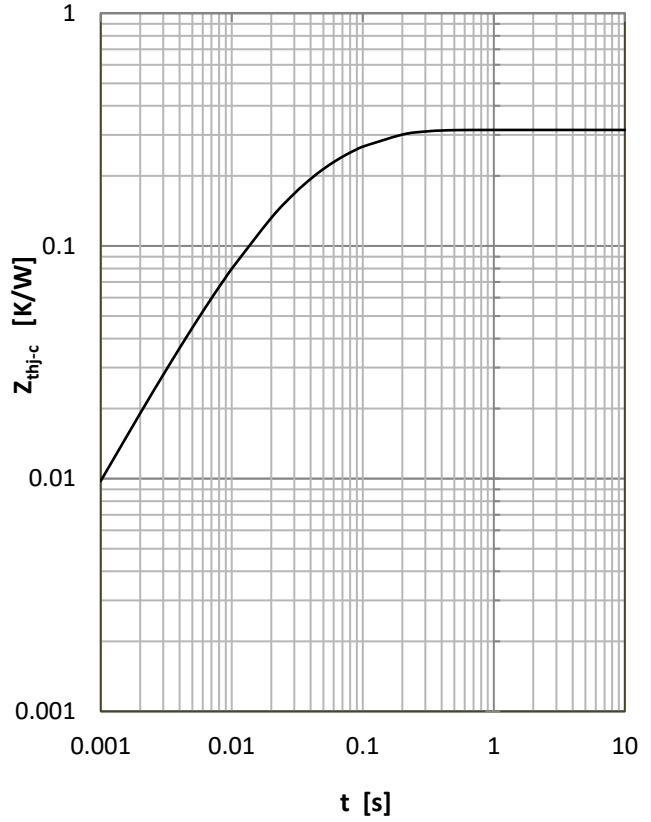


**Curve Characteristics**

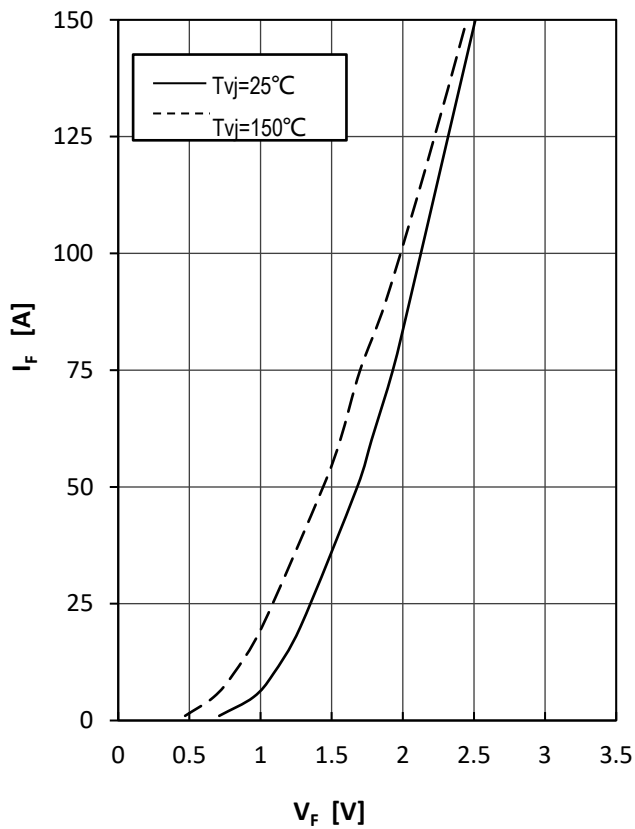
**Fig5. RBSOA**



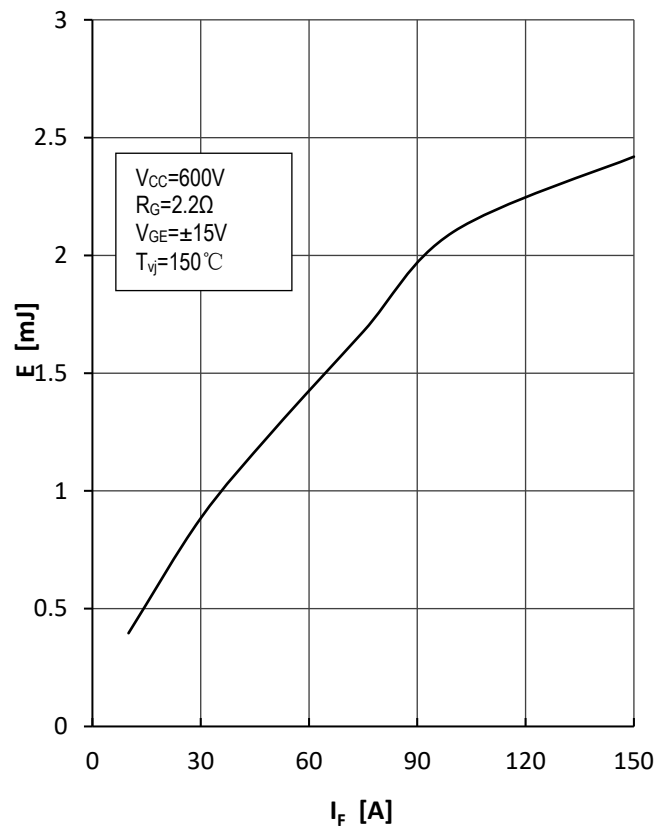
**Fig 6. IGBT Transient Thermal Impedance**



**Fig7.Diode Foward Characteristics**

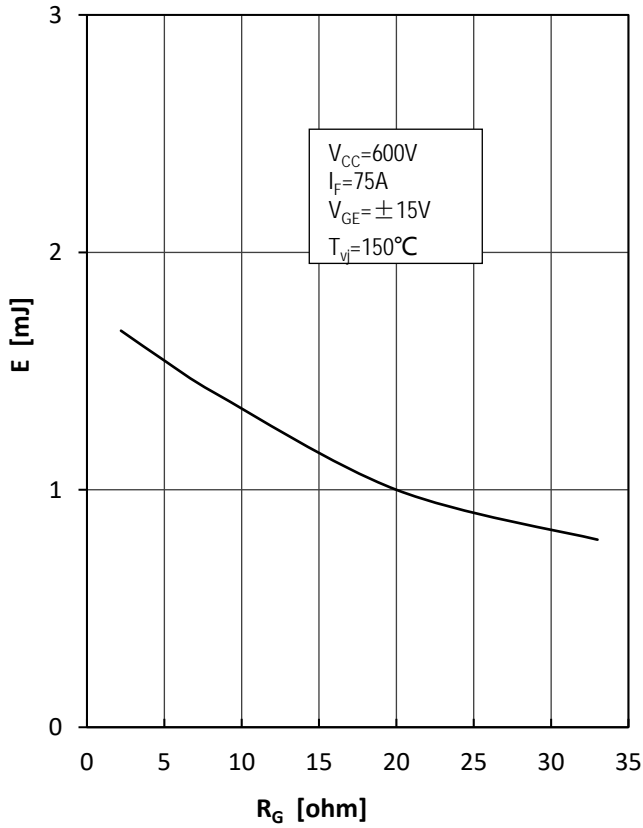


**Fig8.Diode Switching Loss vs.IF**

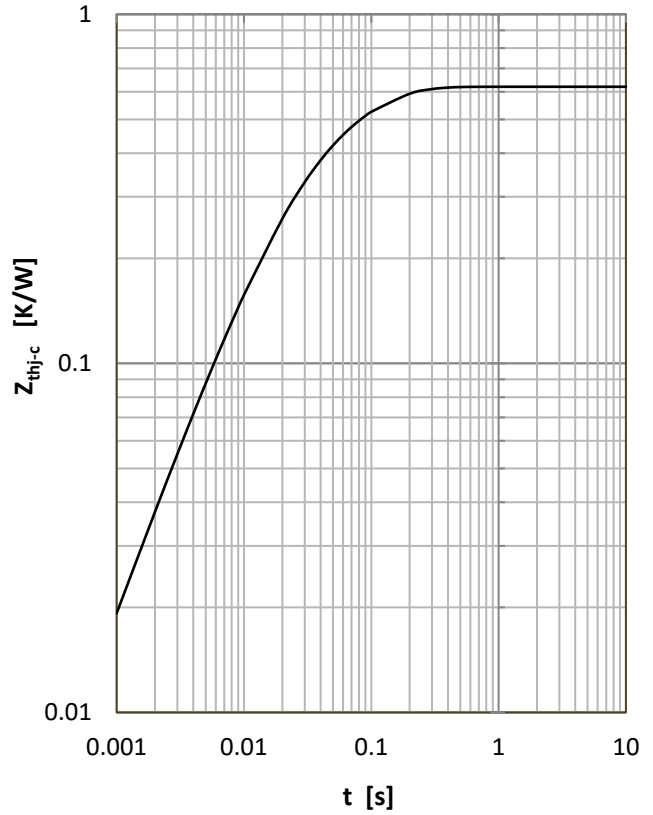


**Curve Characteristics**

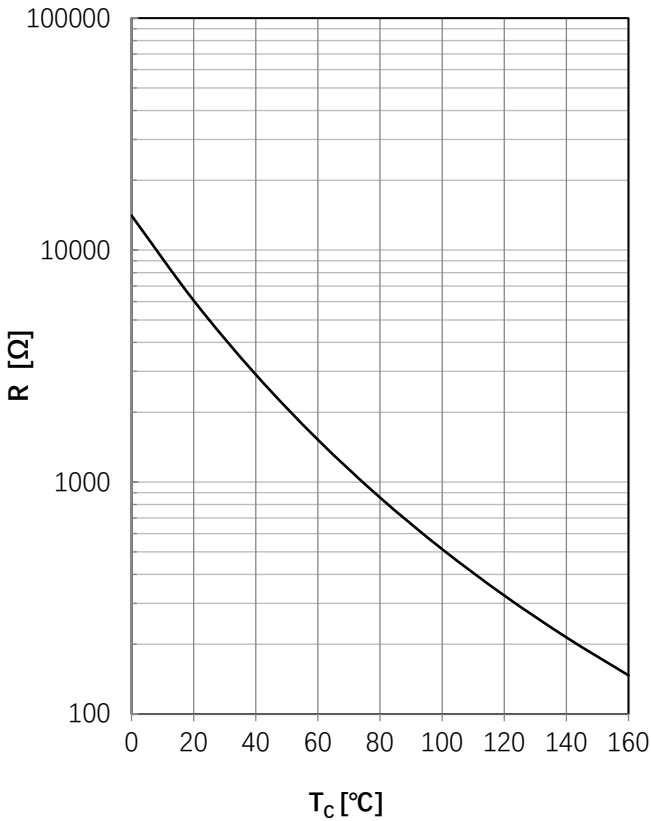
**Fig9. Diode Switching Loss vs. R<sub>G</sub>**



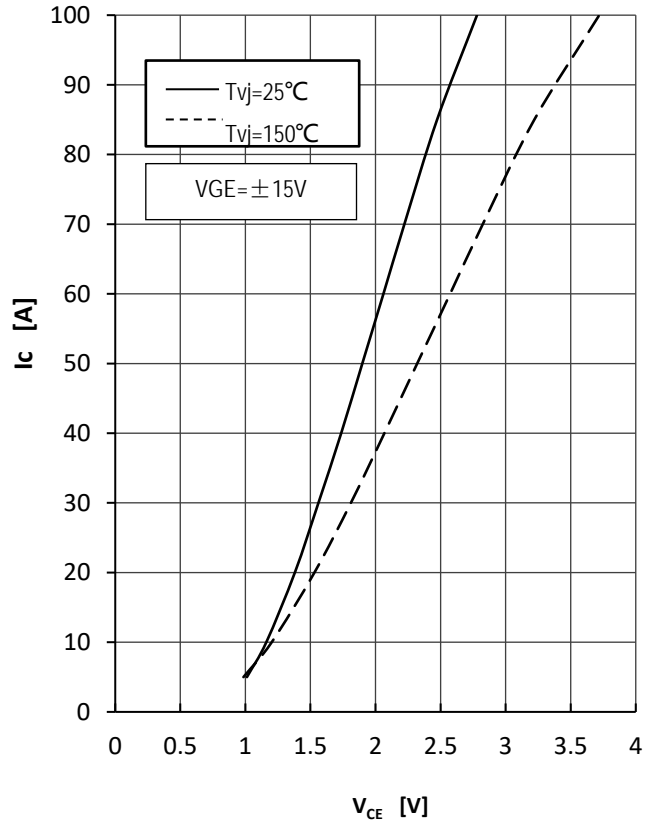
**Fig10. Diode Transient Thermal Impedance**



**Fig 11. NTC Temperature Characteristic**

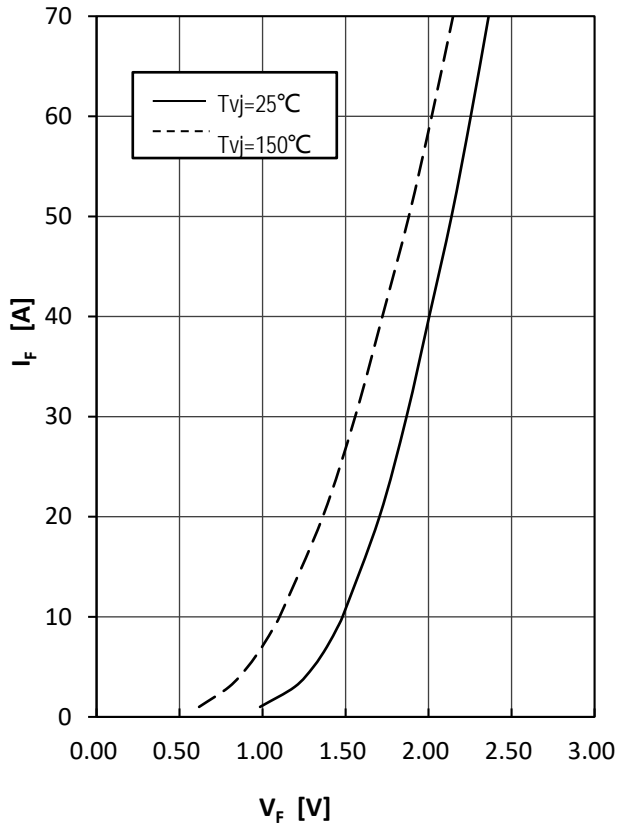


**Fig12. IGBT-brake-chopper Output Characteristics**

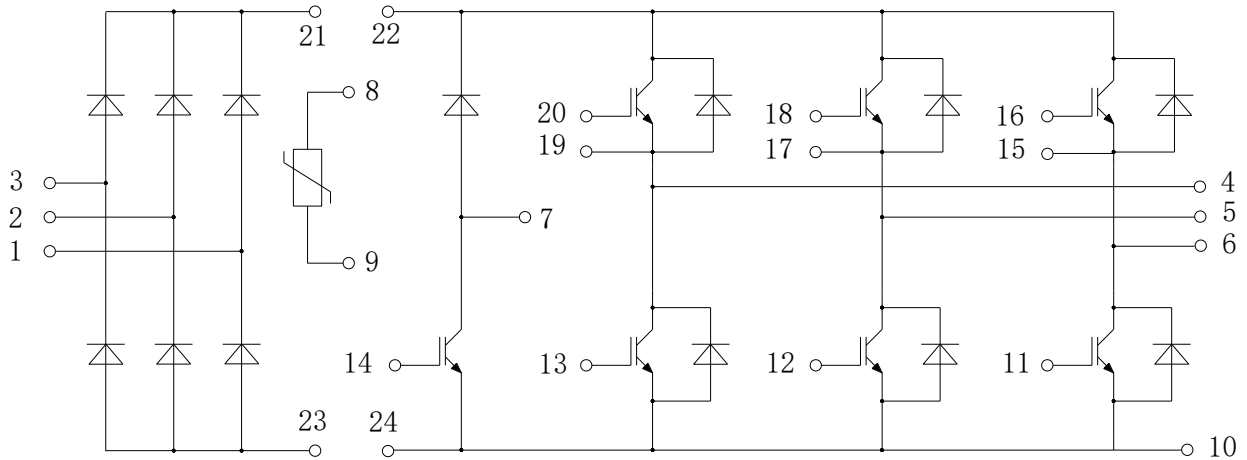


### Curve Characteristics

Fig13. Diode-brake-chopper Forward Characteristics



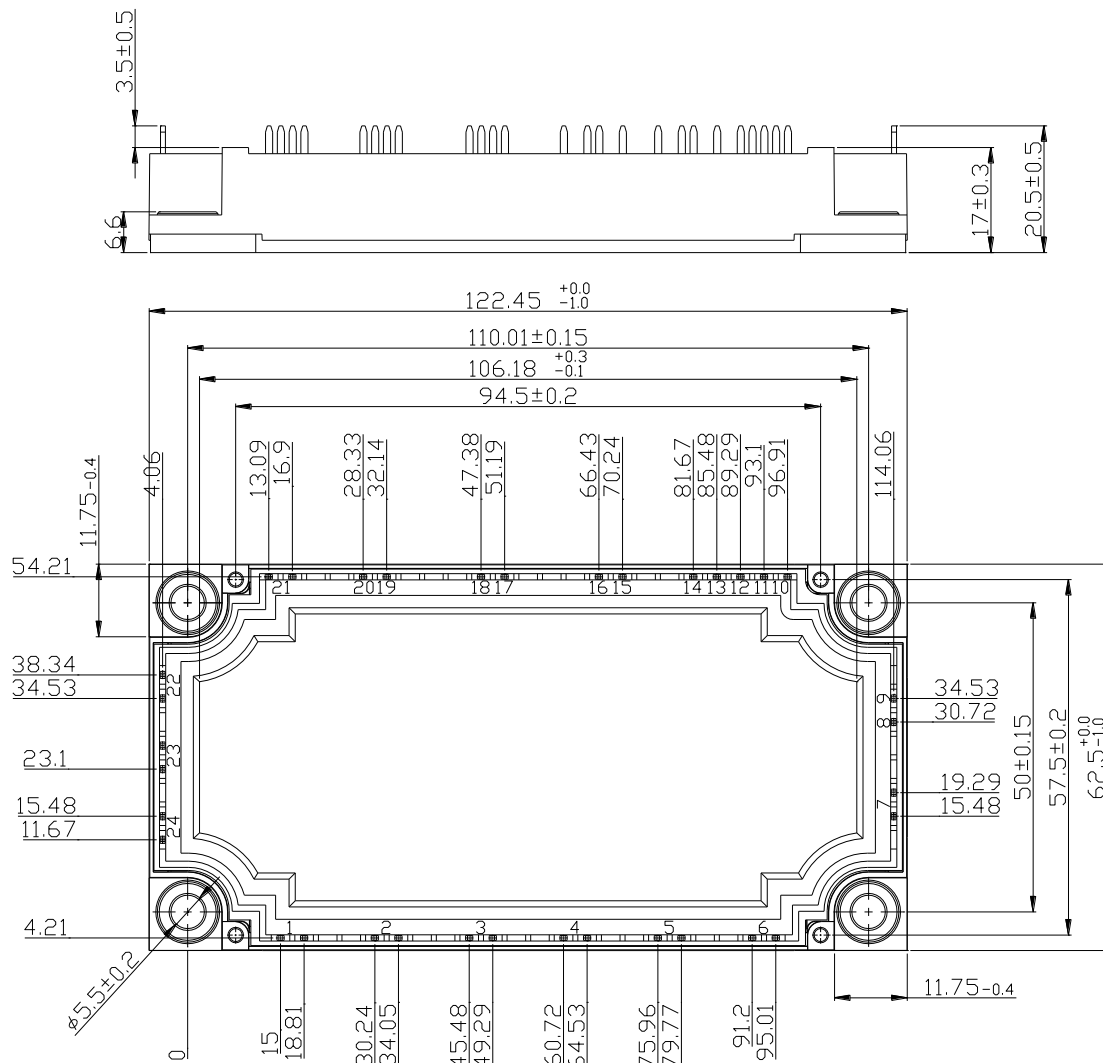
### Circuit Diagram



### Package Dimensions

Dimensions in mm

# E2A



## Ordering Information

Device	Packing
Part Number-BP	Bulk: 6pcs/Box ; 36pcs/Ctn

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